

MvpLED™ SL-V-B35AD

High Power BLUE LED

BLUE LED

Introduction

The advantages of the patented and proprietary MvpLED™ design especially in Thermal management, and Optical efficacy, are realized in light quality, lifetime, color consistency, reliability and overall efficiency of the luminaire. Available in Blue, Green and UV SemiLEDs high efficiency chips bring real benefits to any lamp or luminaire manufacturer.

Among pure metals at room temperature, copper has the second highest electrical and thermal conductivity after silver. Furthermore, due to the high thermal conductivity of the copper alloy layer, the heat generated in our device is effectively conducted. This is a major advantage for any lamp or luminaire manufacturer. No matter how good a thermal design is, if the contact material to the junction is a poor conductor then the cooling effects of the heat-sink are significantly reduced.

Using a proprietary surface texturing technique, SemiLEDs LEDs maximize light extraction and efficiency. Coupled with a minimal use of Sapphire and a 90% efficient Reflective Layer, SemiLEDs chips exhibit an almost perfect Lambertian radiation pattern.

SemiLEDs' patented and unique process uses a limited amount of Sapphire, which can be recycled and reused multiple times, significantly reducing the Carbon footprint. The reduced dependence on Sapphire also removes a thermal management bottleneck while providing the most environmentally friendly LED on the market.

RoHS and REACH Compliant

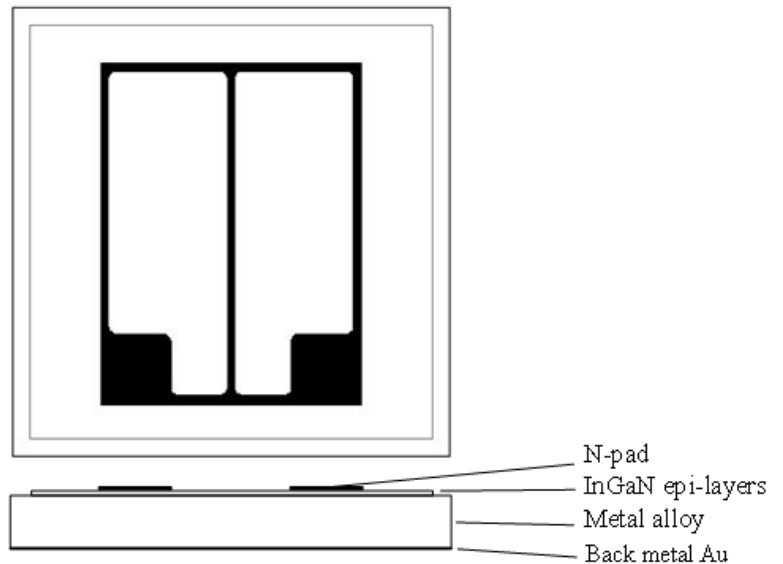
Feature

Metal alloy device-----	Low cost high thermal conductivity
Thickness 95 μm -----	Consolidated metal alloy
P-N junction high at 90 μm -----	Silver epoxy die attachment compatible
One pad structure-----	Low package cost
Nearly Perfect Lambertian emission pattern -----	Ideal for white light design
Patterned surface -----	Maximum light extraction

Applications

LCD backlight
 Digital Camera Flash light
 High Power LED
 Automotive lighting
 Signalling
 Signage
 Miniature Light Engine

Chip Mechanical Diagram



Mechanical Specifications

P-N junction area	800 μm X 800 μm	$\pm 20 \mu\text{m}$
Base area	860 μm X 860 μm	$\pm 50 \mu\text{m}$
Chip thickness	95 μm	$\pm 15 \mu\text{m}$
Bond pad size	140 μm	$\pm 10 \mu\text{m}$
Bond pad thickness	2.5 μm	$\pm 0.5 \mu\text{m}$
Junction height	90 μm	$\pm 15 \mu\text{m}$

Optical and Electrical Characteristics at 350mA, Ta at 25°C

Parameter	Symbol	Min	Typ	Max	Remark
Forward voltage:	Vf		3.4	3.8	Volt
Spectra half width	$\Delta\lambda$		20	40	nm
Reverse current	Ir			2 μ A	Vr= 5 Volt

Measured by SemiLEDs on bare chip

Absolute Maximum Ratings, Ta at 25°C

Forward Current (DC)	350 mA
Peak Forward Current (1/10 duty cycle @ 1KHz)	700 mA
LED Junction Temperature	125°C
Reverse Voltage	5 V
Operating Temperature	-40°C to +110°C
Storage Temperature	-40°C to +110°C
Temperature during packaging (reflow)	280°C < 10 sec

Maximum ratings are strongly package dependent and may differ between different packaged devices. The values given were collected by SemiLEDs' in-house package.

BIN Table (Output Power at 350mA, Ta at 25°C)

Wd Range(nm)	290-350mW	350-400mW	400-450mW
450-452.5	AE	AF	AG
452.5-455	BE	BF	BG
455-457.5	CE	CF	CG
457.5-460	DE	DF	DG
460-462.5	EE	EF	EG
462.5-465	FE	FF	FG
465-467.5	GE	GF	
467.5-470	HE	HF	
470-472.5	IE	IF	
472.5-475	JE	JF	

Performance Diagram

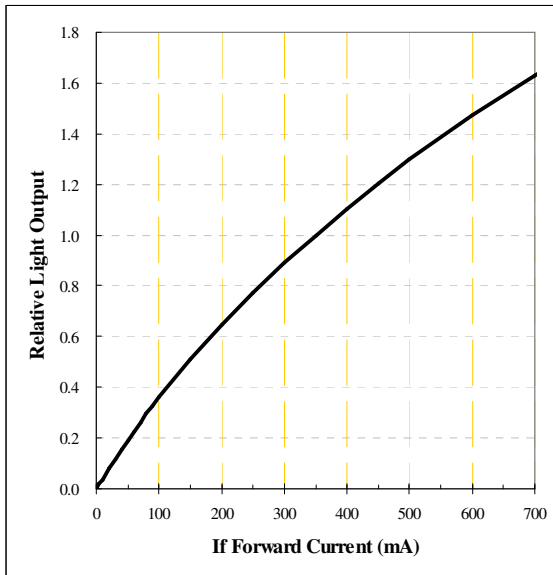


Fig-1 Relative Output Power vs. Forward Current.

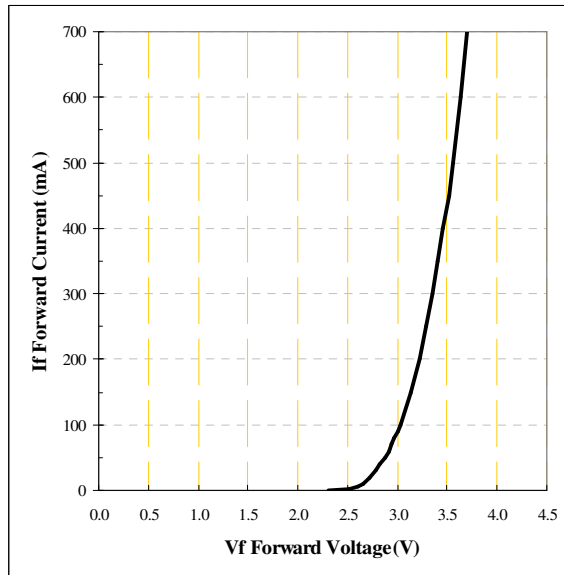


Fig-2 Forward Current vs. Forward Voltage.

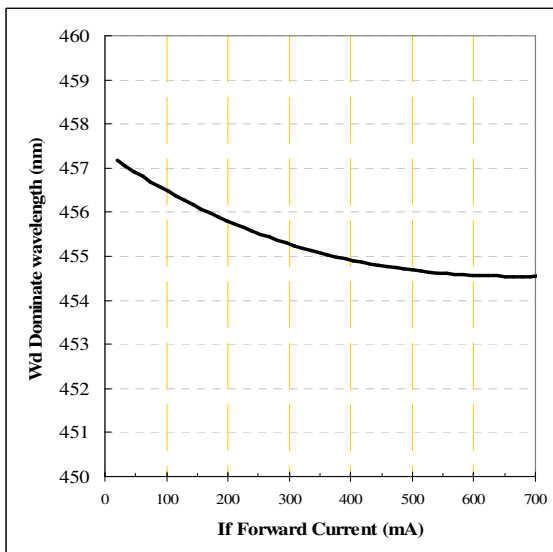


Fig-3 Forward Dominate Wavelength vs. Forward Current.

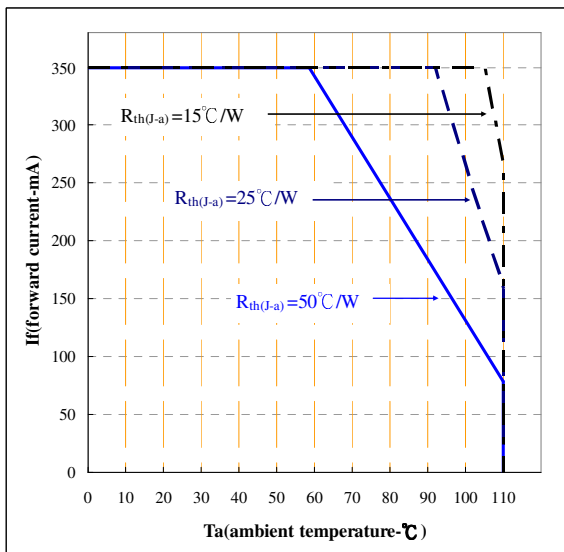


Fig-4 Maximum Driving Forward DC Current vs. Ambient Temperature.

Note:

- Minimum and maximum value refers to the limits and set up of SemiLEDs' testers. All other measurement data are defined as long-term production mean values and are only given for information.
- A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system. Life support devices or systems are intended (i) to be implanted in the human body, or (ii) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered. Components used as a critical component must be approved in writing by SemiLEDs.

About Us

SemiLEDs is a manufacturer of ultra-high bright LED chips with state of the art fabrication facilities in Hsinchu Science Park, Taiwan. SemiLEDs specializes in the development and manufacturing of metal alloy vertical LED chips in blue (white), green and UV using our patented and proprietary MvpLED™ technology. This unique design allows for higher performance and longer lumen maintenance. SemiLEDs new high power I-core MvpLEDs™ can deliver over 120lm/W. In December 2008 The World Economic Forum recognized SemiLEDs innovations with the 2009 Technology Pioneer Award.



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